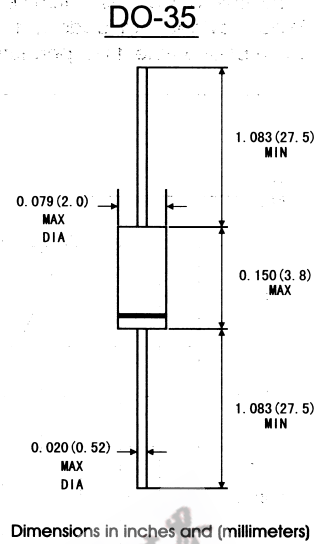


FEATURES

- The zener voltage are graded according to the international E24 standard .Other voltage tolerance and higher zener voltage on request.

MECHANICAL DATA

- Case:** DO-35 glass case
- Polarity:** Color band denotes cathode end
- Weight:** Approx. 0.13gram



ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES)(TA=25°C)

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation at TA=50°C	P _{tot}	500 ¹⁾	mW
Junction temperature	T _J	175	°C
Storage temperature range	T _{STG}	-65 to + 175	°C

1)Valid provided that at a distance of 8mm from case are kept at ambient temperature

ELECTRICAL CHARACTERISTICS(TA=25°C)

	Symbols	Min.	Typ.	Max.	Units
Thermal resistance junction to ambient	R _{θJA}			300 ¹⁾	K/W
Forward voltage at I _F =100mA	V _F			1	V

1)Valid provided that leads at a distance of 8mm from case are kept at ambient temperature



BXZ55... SILICON PLANAR ZENER DIODES

Type	Zener Voltage Range ¹⁾			Dynamic resistance			Reverse leakage current			Temp coefficient of zener voltage
	V _{ZNOM}	I _{ZT} for V _{ZT} 2)		r _{Zjt} and r _{Zjk} at I _{Zk}			I _R and I _{R 2)} at V _R			TK _{VZ}
	V	mA	V	Ω	Ω	mA	μ A	μ A	V	%/K
BZX 55/C 0V8 3)	0.8		0.73.0.83	<8	<50		-	-	-	-0.26...-0.23
BZX 55/C 2V0	2.0	5	1.9.2.1	<85	<600	1	<100	<200	<1	-0.09...-0.06
BZX 55/C 2V4	2.4		2.28.2.56				<50	<100		
BZX 55/C 2V7	2.7		2.5.2.9				<10	<50		
BZX 55/C 3V0	3		2.8.3.2				<4	<40		
BZX 55/C 3V3	3.3		3.1.3.5				<2	<40		
BZX 55/C 3V6	3.6		3.4.3.8				<1	<20		
BZX 55/C 3V9	3.9		3.7.4.1				<0.5	<10		
BZX 55/C 4V3	4.3		4.0.4.6				<35	<550		
BZX 55/C 4V7	4.7		4.4.5.0				<25	<450		
BZX 55/C 5V1	5.1		4.8.5.4				<10	<200		
BZX 55/C 5V6	5.6		5.2.6.0	<8	<150					
BZX 55/C 6V2	6.2		5.8.6.6	<7	<50					
BZX 55/C 6V8	6.8		6.4.7.2	<7	<50					
BZX 55/C 7V5	7.5		7.0.7.9	<10	<70					
BZX 55/C 8V2	8.2		7.7.8.7	<15	<70					
BZX 55/C 9V1	9.1		8.5.9.6	<20	<90					
BZX 55/C 10	10		9.4.10.6	<26	<110					
BZX 55/C 11	11		10.4.11.6	<30	<110					
BZX 55/C 12	12		11.4.12.7	<40	<170					
BZX 55/C 13	13	12.4.14.1	<50	<170						
BZX 55/C 15	15	13.8.15.6	<55	<220						
BZX 55/C 16	16	15.3.17.1			<0.1	<2	2.0	0.03.0.06		
BZX 55/C 18	18	16.8.19.1					3.0	0.03.0.07		
BZX 55/C 20	20	18.8.21.2					5.0	0.03.0.07		
								6.2	0.03.0.08	
								6.8	0.03.0.09	
								7.5	0.03.0.1	
								8.2	0.03.0.11	
								9.1		
								10.0		
								11.0		
								12		
								13		
								15		

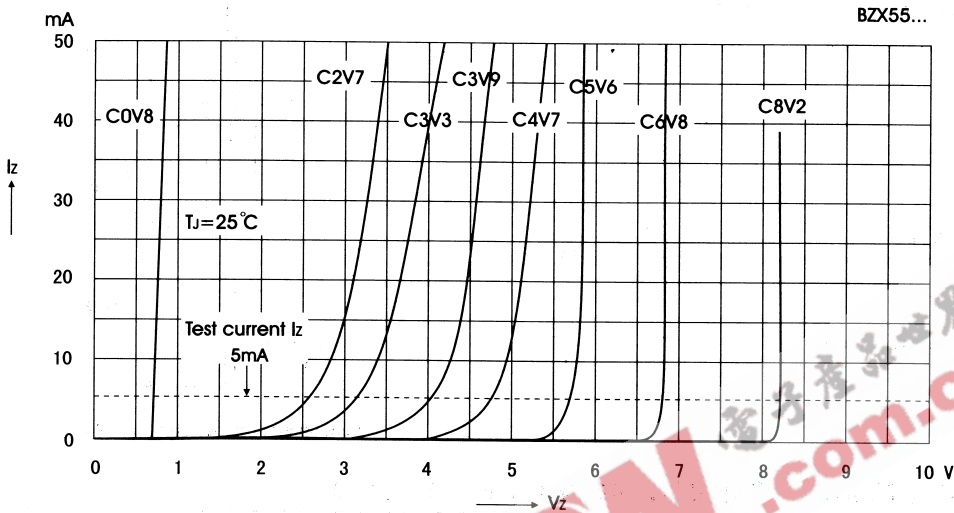


BZX55... SILICON PLANAR ZENER DIODES

BZX 55/C 22	22	5	20.8.23.3	<55	<220	1	<2	16	0.04.0.12
BZX 55/C 24	24		22.8.25.6	<80				18	
BZX 55/C 27	27		25.1.28.9	<80				20	
BZX 55/C 30	30		28.32					22	
BZX 55/C 33	33		31.35					24	
BZX 55/C 36	36		34.38					27	
BZX 55/C 39	39	2.5	37.41	<500	0.5	<0.1	<5	30	
BZX 55/C 43	43		40.46	<500			33		
BZX 55/C 47	47		44.50	<600			36		
BZX 55/C 51	51		48.54	<700			39		
BZX 55/C 56	56		52.60	<700			43		
BZX 55/C 62	62		58.66	<1000			47		
BZX 55/C 68	68		64.72				51		
BZX 55/C 75	75		70.79				56		
BZX 55/C 82	82		77.87				<1500	62	
BZX 55/C 91	91		1	85.96			<2000	0.1	<10
BZX 55/C 100	100	94.106		<5000	75				
BZX 55/C 110	110	104.116		<5000	82				
BZX 55/C 120	120	114.127		<5500	91				
BZX 55/C 130	130	124.141		<6000	100				
BZX 55/C 150	150	138.156		<6500	110				
BZX 55/C 160	160	153.171		<7000	120				
BZX 55/C 180	180	168.191		<8500	130				
BZX 55/C 200	200	188.212		<10000	150				
<p>1) Tested with pulses $t_p=20ms$</p> <p>2) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case</p> <p>3) The BZX55-C0V8 is silicon diode with operation in forward direction. Hence, the index of all parameters should be 'F' instead of 'Z'. Connect the cathode lead to the negative pole.</p>									

BXZ55... SILICON PLANAR ZENER DIODES

BREAKDOWN CHARACTERISTICS AT T_J=CONSTANT(PULSED)



BREAKDOWN CHARACTERISTICS AT T_J=CONSTANT(PULSED)

